

April 2015

FDD8445

N-Channel PowerTrench® MOSFET 40V, 50A, 8.7m Ω

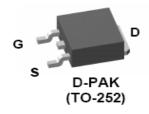
Features

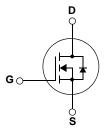
- $R_{DS(ON)} = 6.7 \text{ m}\Omega$ (Typ), $V_{GS} = 10V$, $I_D=50A$
- $Q_{g(10)} = 45nC \text{ (Typ)}, V_{GS}=10V$
- Low Miller Charge
- Low Qrr Body Diode
- UIS Capability (Single Pulse/ Repetitive Pulse)
- RoHS Compliant



Applications

- Powertrain Management
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems





Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	±20	V
	Drain Current Continuous (V _{GS} =10v) (Note 1)	70	Α
I_D	Continuous ($V_{GS}=10v$, with $R_{\theta JA}=52^{\circ}C/W$)	15.2	Α
	Pulsed	Figure 4	
E _{AS}	SinglePulseAvalancheEnergy (Note2)	144	mJ
D	Power Dissipation	79	W
P_{D}	Derate above 25°C	0.53	W/ºC
T _J , T _{STG}	Operating and Storage Temperature	-55 to +175	°C

Thermal Characteristics

F	$R_{ heta JC}$	Thermal Resistance, Junction to Case	1.9	°C/W
F	$R_{ heta JA}$	Thermal Resistance, Junction to Ambient TO-252, lin ² copper pad area	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8445	FDD8445	TO-252AA	13"	16mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	40	-	-	V
1	Zero Gate Voltage Drain Current	$V_{DS} = 32V$	-	-	1	μΑ
DSS Zero Gate Voltage Drain Current		$V_{GS} = 0V$ $T_J = 150^{\circ}$	C -	-	250	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	2.8	4	V
		$I_D = 50A, V_{GS} = 10V$	-	6.7	8.7	
R _{DS(ON)}	Drain to Source On Resistance	$I_D = 50A, V_{GS} = 10V,$ $T_J = 175^{\circ}C$	-	12.5	16.3	mΩ

Dynamic Characteristics

Input Capacitance	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		-	3040	4050	pF
Output Capacitance		= UV,	-	295	390	pF
Reverse Transfer Capacitance	1 - 1101112		-	178	270	pF
Gate Resistance	f = 1MHz		-	1.7	-	Ω
Total Gate Charge at 10V	V _{GS} = 0 to 10V		-	45	59	nC
Total Gate Charge at 5V	$V_{GS} = 0 \text{ to } 5V$		-	17	22	nC
Threshold Gate Charge	$V_{GS} = 0$ to $2V$	V _{DD} =20V,	-	5.8	7.6	nC
Gate to Source Gate Charge		$I_D = 50A$	-	12.5	-	nC
Gate Charge Threshold to Plateau			-	9.5	-	nC
Gate to Drain "Miller" Charge			-	10.5	-	nC
	Output Capacitance Reverse Transfer Capacitance Gate Resistance Total Gate Charge at 10V Total Gate Charge at 5V Threshold Gate Charge Gate to Source Gate Charge Gate Charge Threshold to Plateau	$\begin{array}{c} \text{Output Capacitance} & \text{V}_{DS} = 25\text{V}, \text{V}_{GS} \\ \text{f} = 1\text{MHz} \\ \\ \text{Gate Resistance} & \text{f} = 1\text{MHz} \\ \\ \text{Total Gate Charge at 10V} & \text{V}_{GS} = 0 \text{ to 10V} \\ \\ \text{Total Gate Charge at 5V} & \text{V}_{GS} = 0 \text{ to 5V} \\ \\ \text{Threshold Gate Charge} & \text{V}_{GS} = 0 \text{ to 2V} \\ \\ \text{Gate to Source Gate Charge} \\ \\ \text{Gate Charge Threshold to Plateau} \end{array}$	$\begin{array}{c} \text{Output Capacitance} \\ \text{Reverse Transfer Capacitance} \\ \text{Gate Resistance} \\ \text{Total Gate Charge at 10V} \\ \text{Total Gate Charge at 5V} \\ \text{Threshold Gate Charge} \\ \text{Gate to Source Gate Charge} \\ \text{Gate Charge Threshold to Plateau} \\ \end{array}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Electrical Characteristics	S T ₁ = 25°C unless otherwise noted
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Switching	g Characteristics					
t _(on)	Turn-On Time		-	-	138	ns
t _{d(on)}	Turn-On Delay Time		-	10	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 20V, I_{D} = 50A$ $V_{GS} = 10V, R_{GS} = 2\Omega$	-	82	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10V, R_{GS} = 2\Omega$	-	26	-	ns
t _f	Turn-Off Fall Time		-	9.6	-	ns
t _{off}	Turn-Off Time		-	-	53	ns

Drain-Source Diode Characteristics

V _{SD} Source to Drain Diode Voltage	Source to Drain Diade Voltage	I _{SD} =50A	-	-	1.25	V
	I _{SD} =25A	-	ı	1.0	V	
t _{rr}	Reverse Recovery Time	I _F = 50A, dI _F /dt=100A/μs	-	-	39	ns
Q _{rr}	Reverse Recovery Charge	I _F = 50A, dI _F /dt=100A/μs	-	-	38	nC

 $\begin{tabular}{ll} \textbf{Notes:} \\ \textbf{1:} & \text{Maximum package current capability is 50A.} \\ \textbf{2:} & \text{Starting T}_J = 25^{\circ}\text{C}, L=0.18\text{mH, I}_{AS}=40\text{A}. \\ \end{tabular}$

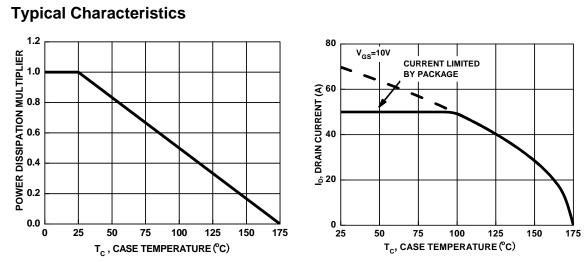


Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs Case Temperature

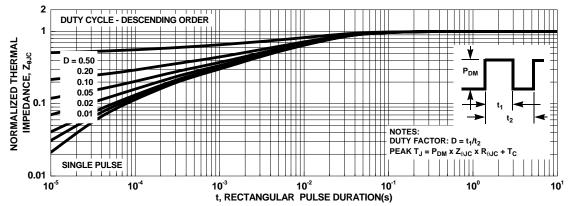


Figure 3. Normalized Maximum Transient Thermal Impedance

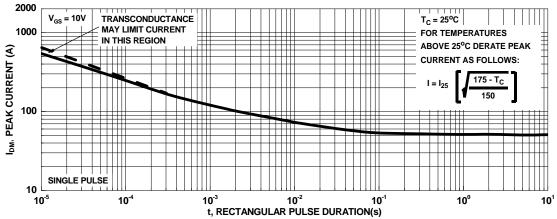
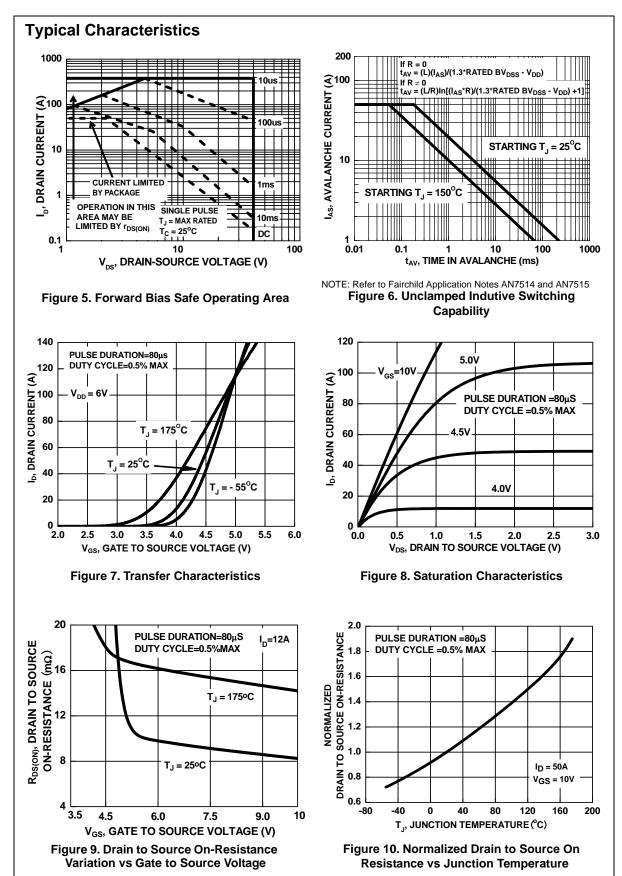


Figure 4. Peak Current Capability



Typical Characteristics

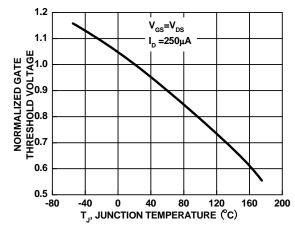


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

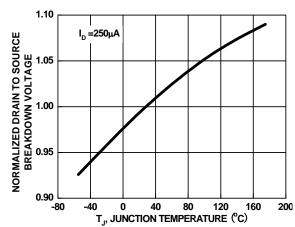


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

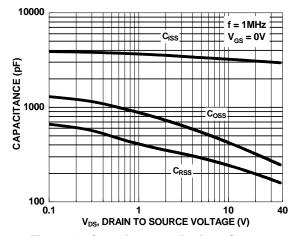


Figure 13. Capacitance vs Drain to Source Voltage

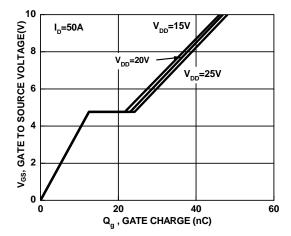
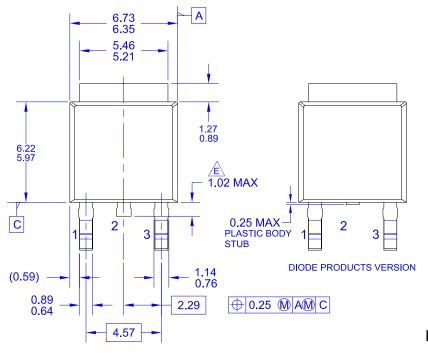
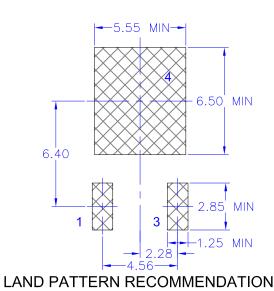
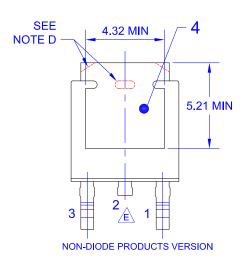


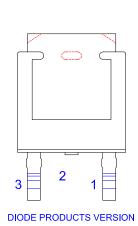
Figure 14. Gate Charge vs Gate to Source Voltage

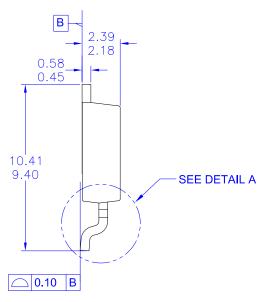




NON-DIODE PRODUCTS VERSION



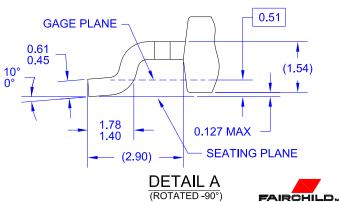




NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252,
- ISSUE C, VARIATION AA.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
- CORNERS OR EDGE PROTRUSION. E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10



SCALE: 12X





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Definition of Terms

Definition of Terms					
Datasheet Identification	Product Status	Definition			
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
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Rev. 174

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